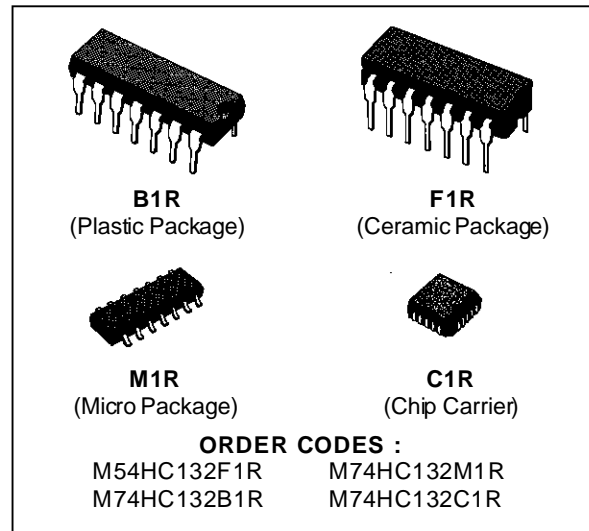


QUAD 2-INPUT SCHMITT NAND GATE

- HIGH SPEED
 $t_{PD} = 11 \text{ ns (TYP.) AT } V_{CC} = 5 \text{ V}$
- LOW POWER DISSIPATION
 $I_{CC} = 1\mu\text{A (MAX.) AT } T_A = 25 \text{ }^\circ\text{C}$
- OUTPUT DRIVE CAPABILITY
 10 LSTTL LOADS
- HIGH NOISE IMMUNITY
 $V_H \text{ (TYP.)} = 0.9 \text{ V AT } V_{CC} = 5 \text{ V}$
- SYMMETRICAL OUTPUT IMPEDANCE
 $|I_{OH}| = I_{OL} = 4 \text{ mA (MIN.)}$
- BALANCED PROPAGATION DELAYS
 $t_{PLH} = t_{PHL}$
- WIDE OPERATING VOLTAGE RANGE
 $V_{CC} \text{ (OPR.)} = 2 \text{ V TO } 6 \text{ V}$
- PIN AND FUNCTION COMPATIBLE
 WITH 54/74LS132



DESCRIPTION

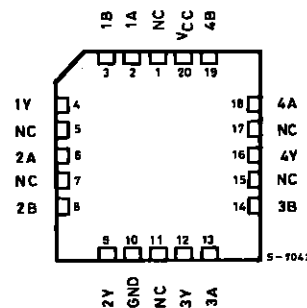
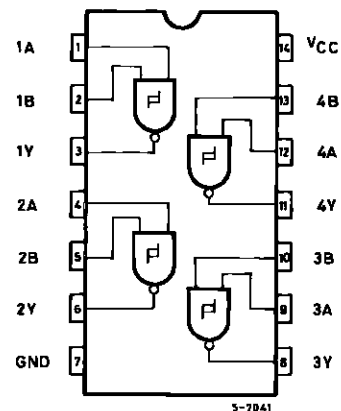
The M54/74HC132 is a high speed CMOS QUAD 2-INPUT SCHMITT NAND GATE fabricated in silicon gate C²MOS technology. It has the same high speed performance of LSTTL combined with true CMOS low power consumption. Pin configuration and function are identical to those of the M54/74HC00.

The hysteresis characteristics (around 20 % V_{CC}) of all inputs allow slowly changing input signals to be transformed into sharply defined jitter-free output signals. All inputs are equipped with protection circuits against static discharge and transient excess voltage.

INPUT AND OUTPUT EQUIVALENT CIRCUIT



PIN CONNECTIONS (top view)



NC =
No Internal
Connection

M54/M74HC132

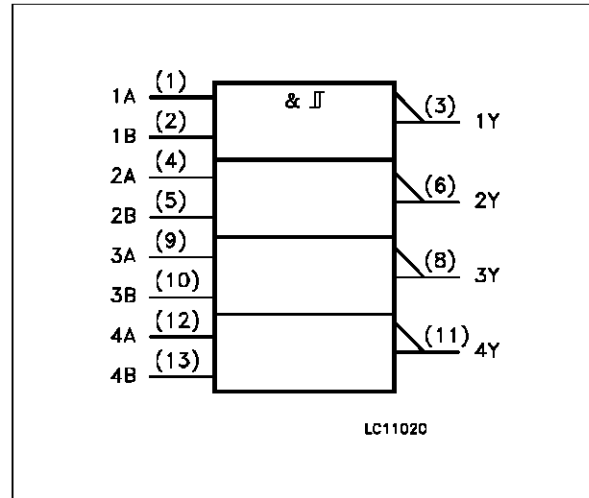
TRUTH TABLE

A	B	Y
L	L	H
L	H	H
H	L	H
H	H	L

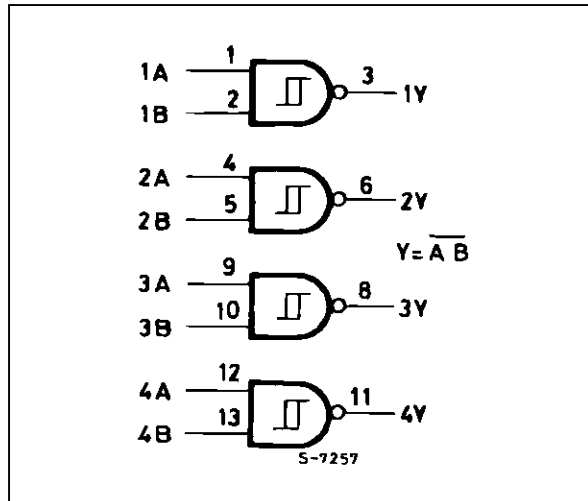
PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1, 4, 9, 12	1A to 4A	Data Inputs
2, 5, 10, 13	1B to 4B	Data Inputs
3, 6, 8, 11	1Y to 4Y	Data Outputs
7	GND	Ground (0V)
14	V _{CC}	Positive Supply Voltage

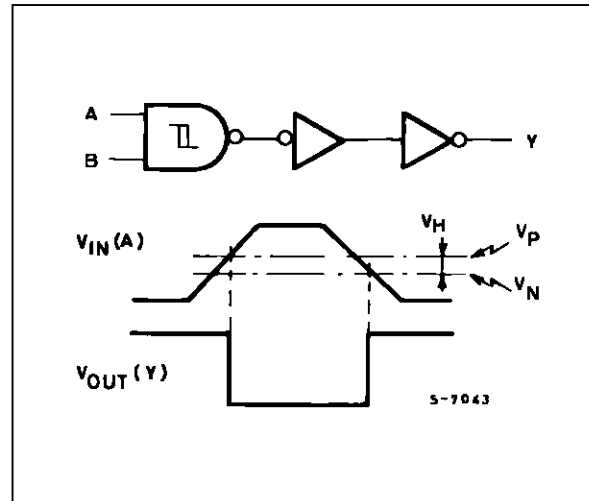
IEC LOGIC SYMBOL



BLOCK DIAGRAM



LOGIC DIAGRAM/WAVEFORM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	-0.5 to +7	V
V _I	DC Input Voltage	-0.5 to V _{CC} + 0.5	V
V _O	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	± 20	mA
I _{OK}	DC Output Diode Current	± 20	mA
I _O	DC Output Source Sink Current Per Output Pin	± 25	mA
I _{CC} or I _{GND}	DC V _{CC} or Ground Current	± 50	mA
P _D	Power Dissipation	500 (*)	mW
T _{stg}	Storage Temperature	-65 to +150	°C
T _L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied.
 (*) 500 mW: ≅ 65 °C derate to 300 mW by 10mW/°C: 65 °C to 85 °C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	2 to 6	V
V _I	Input Voltage	0 to V _{CC}	V
V _O	Output Voltage	0 to V _{CC}	V
T _{op}	Operating Temperature: M54HC Series M74HC Series	-55 to +125 -40 to +85	°C °C
t _r , t _f	Input Rise and Fall Time	No Limits	

DC SPECIFICATIONS

Symbol	Parameter	Test Conditions		Value						Unit		
				T _A = 25 °C 54HC and 74HC			-40 to 85 °C 74HC		-55 to 125 °C 54HC			
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.	
V _P	High Level Threshold Voltage	2.0		1.0	1.25	1.5	1.0	1.5	1.0	1.5	V	
		4.5		2.3	2.7	3.15	2.3	3.15	2.3	3.15		
		6.0		3.0	3.5	4.2	3.0	4.2	3.0	4.2		
V _N	Low Level Threshold Voltage	2.0		0.3	0.65	0.9	0.3	0.9	0.3	0.9	V	
		4.5		1.13	1.6	2.0	1.13	2.0	1.13	2.0		
		6.0		1.5	2.3	2.6	1.5	2.6	1.5	2.6		
V _H	Hysteresis Voltage	2.0		0.3	0.6	1.0	0.3	1.0	0.3	1.0	V	
		4.5		0.6	1.1	1.4	0.6	1.4	0.6	1.4		
		6.0		0.8	1.2	1.4	0.8	1.7	0.8	1.7		
V _{OH}	High Level Output Voltage	2.0	V _I = V _{IH} or V _{IL}	I _O = -20 μA	1.9	2.0		1.9		1.9		V
		4.5			4.4	4.5		4.4		4.4		
		6.0		5.9	6.0		5.9		5.9			
		4.5		I _O = -4.0 mA	4.18	4.31		4.13		4.10		
		6.0			I _O = -5.2 mA	5.68	5.8		5.63		5.60	
V _{OL}	Low Level Output Voltage	2.0	V _I = V _{IH} or V _{IL}	I _O = 20 μA		0.0	0.1		0.1		0.1	V
		4.5				0.0	0.1		0.1		0.1	
		6.0				0.0	0.1		0.1		0.1	
		4.5		I _O = 4.0 mA		0.17	0.26		0.33		0.40	
		6.0			I _O = 5.2 mA		0.18	0.26		0.33		
I _I	Input Leakage Current	6.0	V _I = V _{CC} or GND			±0.1		±1		±1	μA	
I _{CC}	Quiescent Supply Current	6.0	V _I = V _{CC} or GND			1		10		20	μA	

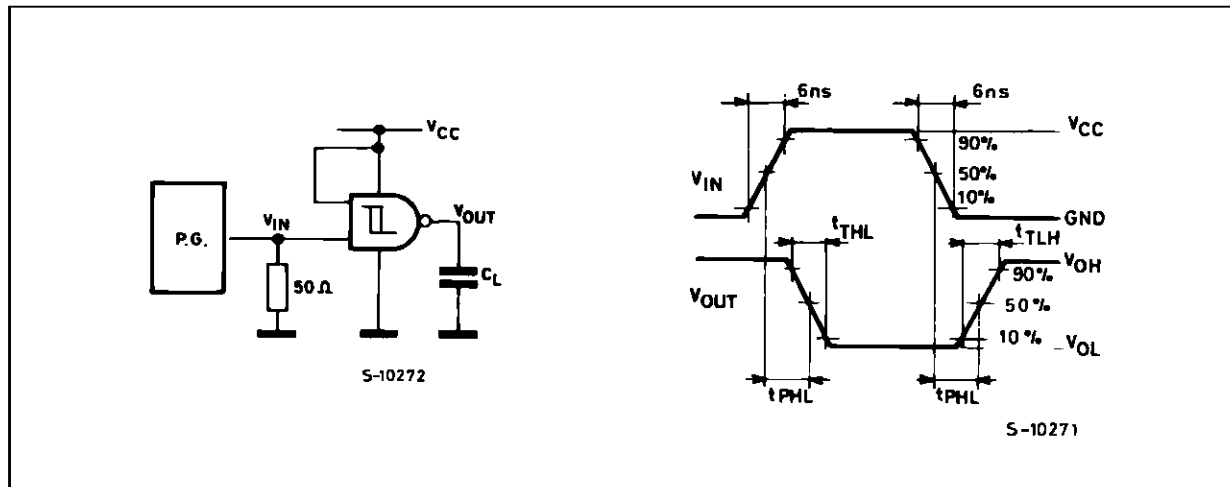
M54/M74HC132

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input t_r = t_f = 6 ns)

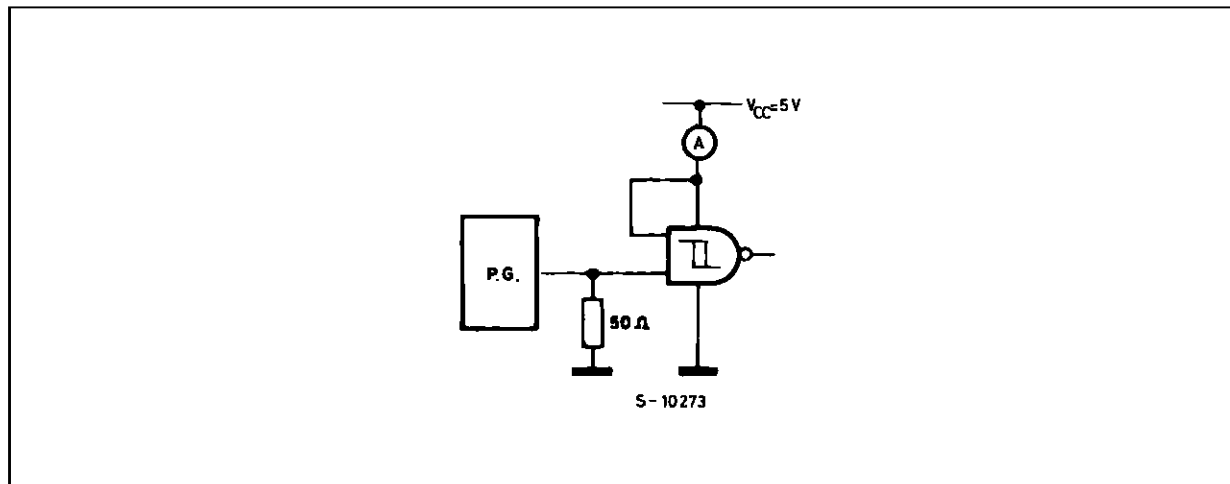
Symbol	Parameter	Test Conditions		Value						Unit	
		V _{CC} (V)		T _A = 25 °C 54HC and 74HC			-40 to 85 °C 74HC		-55 to 125 °C 54HC		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
t _{TLH} t _{THL}	Output Transition Time	2.0			30	75		95		110	ns
		4.5			8	15		19		22	
		6.0			7	13		16		19	
t _{PLH} t _{PHL}	Propagation Delay Time	2.0			52	105		130		160	ns
		4.5			13	21		26		32	
		6.0			11	18		22		27	
C _{IN}	Input Capacitance				5	10		10		10	pF
C _{PD} (*)	Power Dissipation Capacitance				29						pF

(*) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. I_{CC(opr)} = C_{PD} • V_{CC} • f_{IN} + I_{CC}/4 (per Gate)

SWITCHING CHARACTERISTICS TEST CIRCUIT

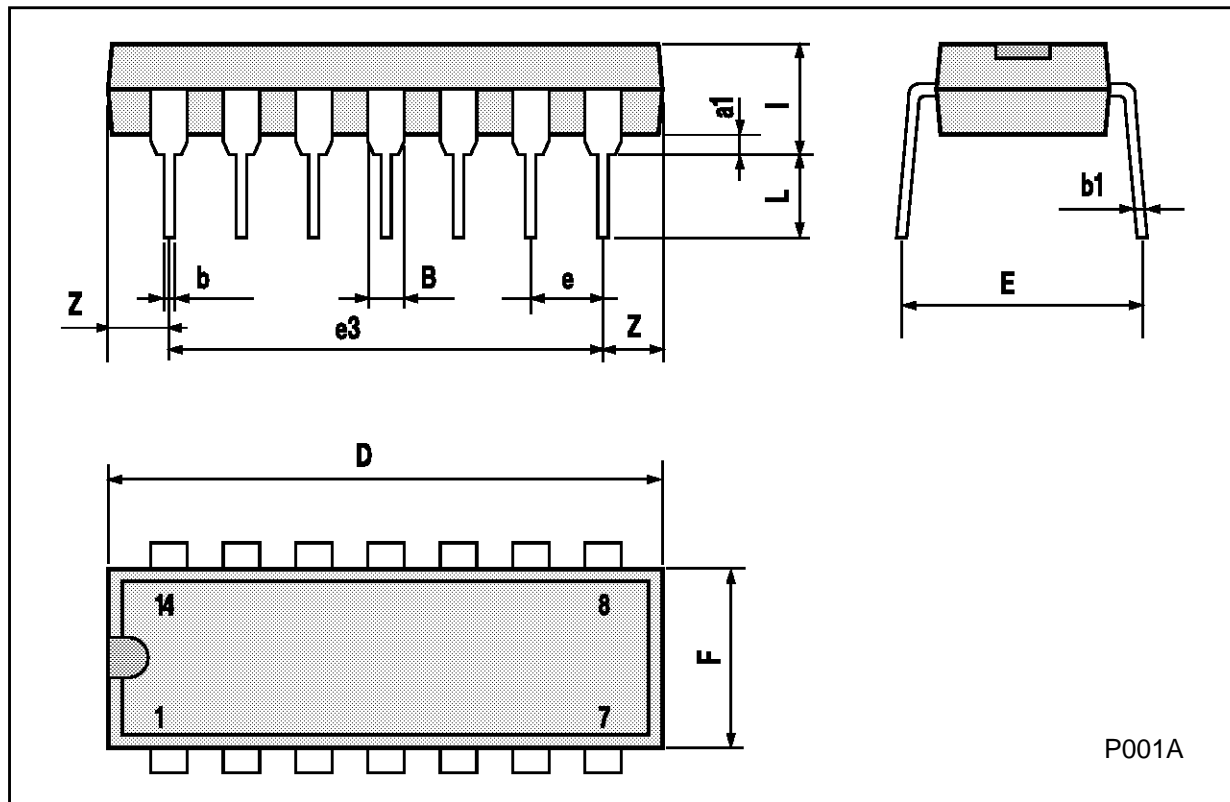


TEST CIRCUIT I_{CC} (Opr.)



Plastic DIP14 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	1.39		1.65	0.055		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		15.24			0.600	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z	1.27		2.54	0.050		0.100



Ceramic DIP14/1 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			20			0.787
B			7.0			0.276
D		3.3			0.130	
E	0.38			0.015		
e3		15.24			0.600	
F	2.29		2.79	0.090		0.110
G	0.4		0.55	0.016		0.022
H	1.17		1.52	0.046		0.060
L	0.22		0.31	0.009		0.012
M	1.52		2.54	0.060		0.100
N			10.3			0.406
P	7.8		8.05	0.307		0.317
Q			5.08			0.200



P053C

SO14 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45° (typ.)					
D	8.55		8.75	0.336		0.344
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		7.62			0.300	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.68			0.026
S	8° (max.)					



PLCC20 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	9.78		10.03	0.385		0.395
B	8.89		9.04	0.350		0.356
D	4.2		4.57	0.165		0.180
d1		2.54			0.100	
d2		0.56			0.022	
E	7.37		8.38	0.290		0.330
e		1.27			0.050	
e3		5.08			0.200	
F		0.38			0.015	
G			0.101			0.004
M		1.27			0.050	
M1		1.14			0.045	



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